

# **N-Channel Power MOSFET**

## **FEATURES**

- · Latest super-junction technology
- Low gate charge capacitance
- High gate noise immunity
- RoHS compliant
- Halogen-free

KEY PERFORMANCE PARAMETERS			
PARAMETER	VALUE	UNIT	
V <sub>DS</sub> @ T <sub>j,max</sub>	650	V	
R <sub>DS(on)</sub> (max)	48	mΩ	
$Q_{g,typ}$	114	nC	

### **APPLICATIONS**

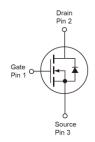
- Switching applications
- HV motor driver
- Industrial











ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	600	V
Gate-Source Voltage		V <sub>GS</sub>	±30	V
Continuous Drain Current	$T_C = 25^{\circ}C$	I <sub>D</sub>	61	А
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	244	Α
Total Power Dissipation @ $T_C = 2$	25°C	P <sub>D</sub>	431	W
Single Pulse Avalanche Energy	Note 2)	Eas	1012	mJ
Single Pulse Avalanche Current	(Note 2)	I <sub>AS</sub>	6.4	А
Operating Junction and Storage	Temperature Range	TJ, TSTG	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	Rejc	0.29	°C/W
Junction to Ambient Thermal Resistance (Note 3)	Reja	50	°C/W

#### Notes:

- 1. Pulse Width ≤ 100µs.
- 2. L = 50mH,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25 $^{\circ}$ C.
- 3. Reja is the sum of the junction-to-case and case-to-ambient thermal resistances. Reja is guaranteed by design while Reja is determined by the user's board design.

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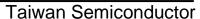
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)				•		l
Drain-Source Breakdown Voltage	$V_{GS} = 0V$ , $I_D = 1mA$	BV <sub>DSS</sub>	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 4.6 \text{mA}$	V <sub>GS(TH)</sub>	4	4.7	6	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V	I <sub>DSS</sub>			100	μA
Drain-Source On-State Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	R <sub>DS(on)</sub>		42	48	mΩ
	V <sub>GS</sub> = 12V, I <sub>D</sub> = 20A			40	44	
Dynamic (Note 5)						
Total Gate Charge	V <sub>DS</sub> = 480V, I <sub>D</sub> = 61A,	Qg		114		
Gate-Source Charge		Qgs		39		nC
Gate-Drain Charge	V <sub>GS</sub> = 10V	Q <sub>gd</sub>		62		
Input Capacitance	$V_{DS} = 300V, V_{GS} = 0V,$ f = 100kHz	C <sub>iss</sub>		5023		
Output Capacitance		Coss		129		pF
Reverse Transfer Capacitance	7 I = 100KHZ	Crss		14		
Gate Resistance	f = 1.0Hz	$R_g$		1.1		Ω
Switching (Note 6)						
Turn-On Delay Time		t <sub>d(on)</sub>		74		
Turn-On Rise Time	$V_{DD} = 300V, R_G = 6.8\Omega,$	t <sub>r</sub>		45		
Turn-Off Delay Time	I <sub>D</sub> = 61A, V <sub>GS</sub> = 10V	t <sub>d(off)</sub>		95		ns
Turn-Off Fall Time		t <sub>f</sub>		34		
Source-Drain Diode						
Forward Voltage (Note 4)	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V	V <sub>SD</sub>		0.9	1.5	V
Reverse Recovery Time	I <sub>S</sub> = 30.5A	t <sub>rr</sub>		508		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Qrr		12		μC

#### Notes:

- 4. Pulse test: Pulse Width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ .
- 5. Defined by design. Not subject to production test.
- 6. Switching time is essentially independent of operating temperature.

## **ORDERING INFORMATION**

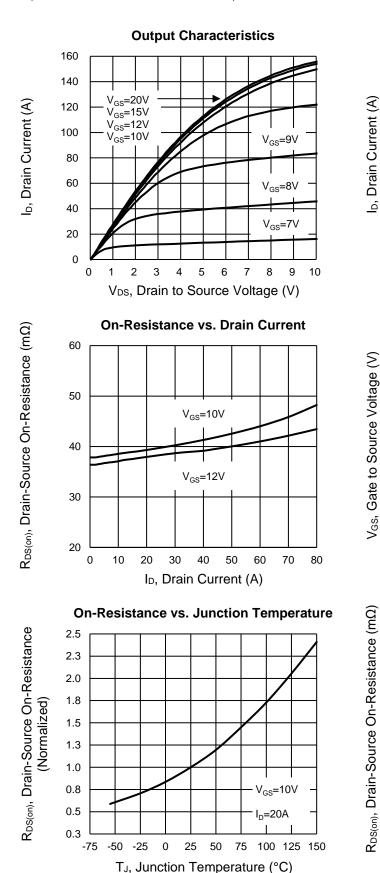
ORDERING CODE	PACKAGE	PACKING
TSM60NE048PW C0G	TO-247	30pcs / Tube

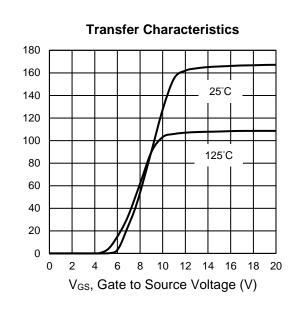


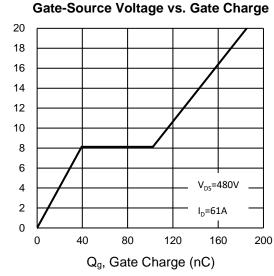


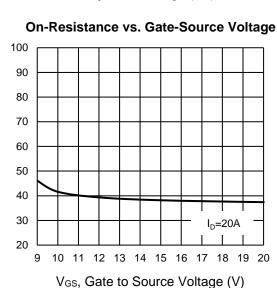
#### **CHARACTERISTICS CURVES**

(T<sub>C</sub> = 25°C unless otherwise noted)

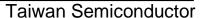








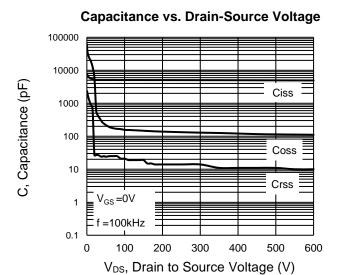
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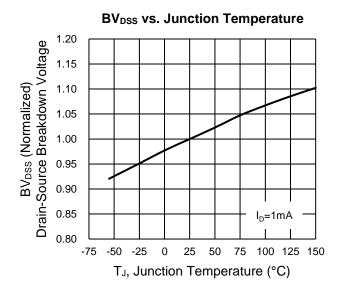




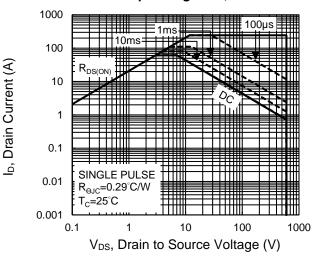
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(T<sub>C</sub> = 25°C unless otherwise noted)





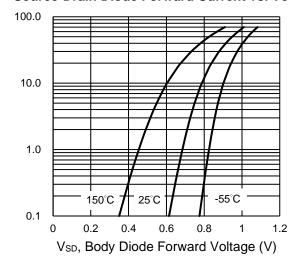
## Maximum Safe Operating Area, Junction-to-Case



Normalized Effective Transient

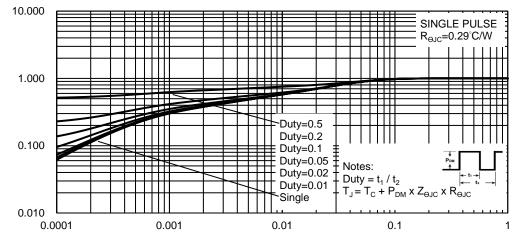
Thermal Impedance, Zeuc

## Source-Drain Diode Forward Current vs. Voltage



## Normalized Thermal Transient Impedance, Junction-to-Case

Reverse Drain Current (A)

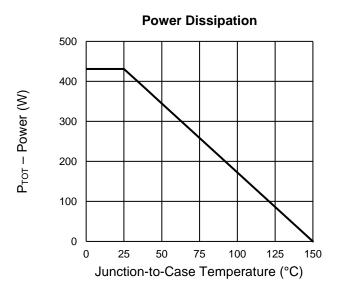


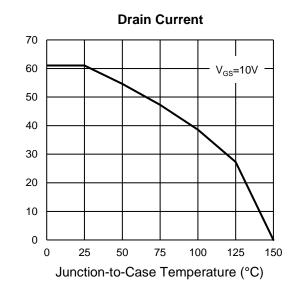
t, Square Wave Pulse Duration (sec)



## **CHARACTERISTICS CURVES**

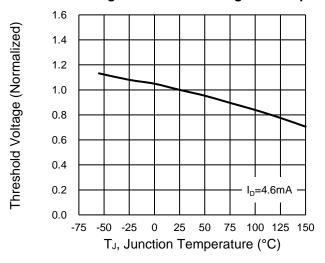
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$ 





Ip-Drain Current (A)

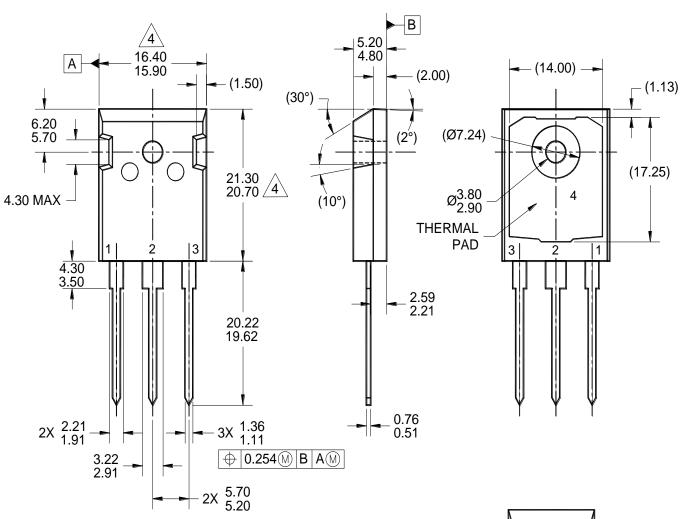
## Normalized gate threshold voltage vs Temperature





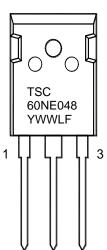
## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

#### TO-247



### NOTES: UNLESS OTHERWISE SPECIFIED

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. PACKAGE OUTLINE REFERENCE: JEDEC TO-247, VARIATION AD, ISSUE E.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
- 5. DWG NO. REF: HQ2SD07-TO247AD-071 REV C.



MARKING DIAGRAM

Y = YEAR CODE

WW = WEEK CODE (01~52)

L = LOT CODE (1~9, A~Z)

F = FACTORY CODE



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